REVISION RECORD		
REV	DESCRIPTION	DATE
0	INITIAL RELEASE	06/12/96
A	• PAGE 2, ADDED PARAGRAPHS 3.2.1 AND 3.2.2. PARAGRAPH 3.3.b, ADDED "(SEE PARAGRAPH 3.2)". • PAGE 4, PARAGRAPH 4.4.2, GROUP B INSPECTION, REDEFINED. PARAGRAPH 4.4.3, GROUP D INSPECTION, REDEFINED. PARAGRAPH 4.5, SOURCE INSPECTION, REDEFINED. • PAGE 6, ADDED θja AND θjc TO FIGURE 1, TO39 CASE OUTLINE. • PAGE 7, ADDED θja AND θjc TO FIGURE 2, TO3 CASE OUTLINE. • PAGE 12, TABLE I, ELECTRICAL CHARACTERISTICS (PRE-IRRADIATION), DATASHEET CHANGES TO PARAMETERS. • PAGE 13, TABLE IA, ELECTRICAL CHARACTERISTICS (POST-IRRADIATION), DATA SHEET CHAGNES TO PARAMETERS. • PAGE 14, TABLE III, ELECTRICAL TEST REQUIREMENTS, ADDED SUBGROUPS 4, 5, AND 6 TO FINAL ELECTRICAL TEST REQUIREMENTS AND GROUP A TEST REQUIREMENTS. ENGINEERING CHANGE TO TABLE II, POST BURN-IN ENDPOINTS AND DELTA LIMIT REQUIREMENTS, VRLNIE PARAMETER.	03/10/98
B	• PAGE 4, AMENDED PARAGRAPHS 4.1 AND 4.1.1 TAKING EXCEPTION TO ANALYSIS OF CATASTROPHIC FAILURES.	05/01/98
C	• PAGE 7 AND 8, FIGUIRE 1, 2 CHANGES θja AND θjc.	09/27/99
D	• PAGE 3, PARAGRAPHS 3.2.1, 3.2.2, FIGURES 1, 2 REMOVED. • PAGE 4, PARAGRAPH 3.7, CHANGED VERBIAGE FROM "SPECIFIED IN TABLE III" TO "AND AS SPECIFIED IN TABLE III HEREIN", LINE 2. PARAGRAPH 3.9, ADDED "HEREIN" AFTER "TABLE II" LINE 2. • PAGE 5, PARAGRAPH 4.3, ADDED "HEREIN" AFTER "TABLE III", LINE 2. PARAGRAPH 4.4.1, ADDED "HEREIN" AFTER "TABLE III", LINE 2. PARAGRAPH 4.4.2.2, CHANGED VERBIAGE IN LINE 1 FROM "ALL FOOTNOTES OF TABLE IIA IN MIL-STD-883". • PAGE 5, PARAGRAPH 4.4.3.2, CHANGED VERBIAGE IN LINE 1 FROM "ALL FOOTNOTES OF TABLE IV OF MIL-STD-883" TO "ALL FOOTNOTES PERTAINING TO TABLE IV IN MIL-STD-883".	12/13/99
E	• CONVERSATION FROM WORD PERFECT TO MICROSOFT WORD. INCREASED SPEC PAGES TO 15 TOTAL. • PAGE 1, CORRECTED CAGE CODE # FROM 94155 TO 64155. • PAGE 2, AN ADDITIONAL REVISION RECORD PAGE WAS ISNTALLED. (SEE NEXT PAGE REVISION CONTINUED)	05/31/02

CAUTION: ELECTROSTATIC DISCHARGE SENSITIVE PART

REVISION	PAGE NO.	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15		
INDEX	REVISION	**N**	**N**	**N**	**N**	**N**	**N**	**N**	**N**	**N**	**N**	**N**	**N**	**N**	**N**	**N**		
REVISION	PAGE NO.																	
INDEX	REVISION																	

				ANALOG DEVICES INC.	
	ORIG				
	DSGN			TITLE:	
	ENGR			**MICROCIRCUIT, LINEAR,**	
	MFG			**RH1086M, LOW DROPOUT**	
	CM			**POSITIVE ADJUSTABLE REGULATOR**	
	QA			SIZE / CAGE CODE / DRAWING NUMBER	REV
	PROG			**64155** / **05-08-5021**	**O**
APPLICATION	FUNCT	SIGNOFFS	DATE	CONTRACT:	

FOR OFFICIAL USE ONLY

REVISION RECORD		
REV	DESCRIPTION	DATE
E	• PAGE 3, PARAGRAPH 3.2.1 ADDED "OPTION 1" AND PARAGRAPH 3.2.2, ADDED "OPTION 2". • PAGE 4, PARAGRAPH 3.4, MOVED PARAGRAPH AND NOTES FROM PAGE 3. PARAGRAPH 3.4, MOVED PARAGRAPH AND NOTES FROM PAGE 3. PARAGRAPH 3.6, TABLE IA CHANGED TO TABLE II. PARAGRAPH 3.7, TABLE III CHANGED TO TABLE IV. PARAGRAPH 3.8, BROKEN DOWN INTO 2 PARAGRAPHS, 3.8.1 AND 3.8.2, FOR THE 2 BURN-IN OPTIONS. PARAGRAPH 3.9, TABLE II CHANGED TO TABLE III. PARAGRAPH 3.11.1 WAS CHANGED FROM "…dosage rate of approximately 20 Rads per second" TO "…dosage rate of less than or equal to 10 Rads per second". • PAGE 5, PARAGRAPHS 4.1 THROUGH 4.4.2 CHANGES WERE DONE TO CLARIFY GROUP SAMPLING. PARAGRAPHS 4.4.2.1 THOUGH 4.4.3 CHAGNES WERE DONE TO CLARIGY GROUP SAMPLING. • PAGE 6: PARAGRAPH 4.4.3.1 CHANGES WERE DONE TO CLARIGY GROUP SAMPLING. PARAGRAPHS 4.6.2 THROUGH 4.6.4 WERE RE-WRITTEN. THESE DATA PROVIDED, AND DATA AVAILABLE. PARAGRAPH 4.6.10 NOTE, ADDED FURTHER EXPLANATION OF MINIMUM DELIVERED DATA. • PAGES 7 THROUGH 12, ALL FIGURES TITLES CHANGED TO HAVE DEVICE OPTIONS AND PACKAGE TYPES AT TOP OF PAGE, AND HAVE ALL FIGURES AT BOTTOM OF PAGE. • PAGE 13, ADDED NOTE ADVISING THE LOCATION OF NOTES FOR TABLE I, II, AND PARAGRAPH 3.4. • PAGE 14, TABLE IA WAS CHANGED TO TABLE II TABLE NOTES NOW REFLECTS TAABLE I AND TABLE II BECAUSE OF CHAGNE ON PAGE 14. • PAGE 15, TABLE II CHAGNED TO TABLE III, TABLE III CHAGNED TO TABLE IV.	05/31/02
F	• PAGE 4, CHANGED INITIAL RATE OF RADS TO 240 RADS/SEC.	03/21/05
G	• PAGE 5, CHANGED IN BOTH PARAGRAPHS 4.2, 4.3 IN CONJUNCTION TO 3.3 CHANGED TO 3.4 AND PARAGRAPH 4.3 CHANGED 3.1.1 TO 3.1 AND 3.2.1 TO 3.1.1	10/04/07
H	• PAGE 4, PARAGRAPH 3.11.1 CHANGED VERBIAGE. PARAGRAPH 3.10.3 CHANGED "ALLOY 42" TO "ALLOY 52" REQUIREMENT ON TO3 PACKAGE.	04/30/08
J	• PAGE 5, PARAGRAPH 4.4.2 CHANGED VERBIAGE. • PAGE 8, FIGURE 2 NOTE 2 ADDED TO LEAD THICKNESS.	07/11/08
K	• PAGE 11, FIGURE 6 STATIC BURN-IN CIRCUIT CHANGED TO 04-06-0302 PER ENG.	04/12/09
L	• PAGE 14, UPDATED REFERENCE VOLTAGE vs. POST IRRADIATION LIMITS IN TABLE II ELECTRICAL CHARACTERISTICS.	12/07/10
M	• PAGE 13, UPDATED TABLE I, PRE-IRRADIATION ELECTRICAL CHARACTERISTICS TO ADD MISSING DROPOUT VOLTAGE LIMITS FOR THE "H" PACKAGE. • PAGE 14, UPDATED TABLE II, POST IRRADIATION ELECTRICAL CHARACTERISTICS TO ADD MISSING DROPOUT VOLTAGE LIMITS FOR THE "H" PACKAGE.	05/02/11
N	REMOVED SOURCE INSPECTION (PARAGRAPH 4.5.1) CHANGED LTC FOOTER TO ANALOG DEVICES INC. ADD OBS TO Option 2 – RH1086MK (TO3 METAL CAN, 2 LEADS) (OBS)	01/15/19
O	**TO CHANGE LINEAR TO ANALOG AND REMOVE SOURCE**	**3/23/21**

1.0 SCOPE:

1.1 This specification defines the performance and test requirements for a microcircuit processed to a space level manufacturing flow.

2.0 APPLICABLE DOCUMENTS:

2.1 Government Specifications and Standards: the following documents listed in the Department of Defense Index of Specifications and Standards, of the issue in effect on the date of solicitation, form a part of this specification to the extent specified herein.

SPECIFICATIONS:

MIL-PRF-38535	Integrated Circuits (Microcircuits) Manufacturing, General Specification for
MIL-STD-883	Test Method and Procedures for Microcircuits
MIL-STD-1835	Microcircuits Case Outlines

2.2 Order of Precedence: In the event of a conflict between the documents referenced herein and the contents of this specification, the order of precedence shall be this specification, MIL-PRF-38535 and other referenced specifications.

3.0 REQUIREMENTS:

3.1 General Description: This specification details the requirements for the RH1085M, 3A LOW DROPOUT POSITIVE ADJUSTABLE REGULATOR, processed to space level manufacturing flow.

The TO3 package on this device cannot meet the cracked glass external visual criteria of MIL-STD-883, Method 2009. Inspection for cracked glass at 100% external visual will not be performed. Instead, a 100% Fine Leak test, per MIL-STD-883, Method 1014, Condition A, and a 100% Gross Leak test, per MIL-STD 883, Method 1014, Condition C, will be performed just prior to shipment.

3.2 Part Number:

3.2.1 Option 1 – RH1086MH (TO39 METAL CAN, 3 LEADS)
3.2.2 Option 2 – RH1086MK (TO3 METAL CAN, 2 LEADS) (OBS)

3.3 Part Marking Includes:

a. LTC Logo

b. LTC Part Number (See Paragraph 3.2)

c. Date Code

d. Serial Number

e. ESD Identifier per MIL-PRF-38535, Appendix A

3.4 The Absolute Maximum Ratings:

Power Dissipation	Internally Limited
Input to Output Voltage Differential	25V
Operating Junction Temperature Range	
Control Section	-55°C to +150°C
Power Transistor	-55°C to +200°C
Storage Temperature Range	-65°C to +150°C
Lead Temperature (Soldering, 10 sec)	+300°C

3.5 Electrostatic discharge sensitivity, ESDS, shall be Class 1.

3.6 Electrical Performance Characteristics: The electrical performance characteristics shall be as specified in **Table I** and **Table II.**

3.7 Electrical Test Requirements: Screening requirements shall be in accordance with 4.1 herein, MIL-STD-883, Method 5004, and as specified in **Table IV** herein.

3.8 Burn-In Requirement:

3.8.1 Option 1 (TO39): Static Burn-in, Figure 5.

3.8.2 Option 2 (TO3): Static Burn-In, Figure 6.

3.9 Delta Limit Requirement: Delta limit parameters are specified in **Table III** herein, are calculated after each burn-in, and the delta rejects are included in the PDA calculation.

3.10 Design, Construction, and Physical Dimensions: Detail design, construction, physical dimensions, and electrical requirements shall be specified herein.

3.10.1 Mechanical / Packaging Requirements: Case outlines and dimensions are in accordance with Figure 1 and Figure 2.

3.10.2 Terminal Connections: The terminal connections shall be as specified in Figure 3 and Figure 4.

3.10.3 Lead Material and Finish: The lead material and finish shall be Kovar for device option 1 and Alloy 52 for device option 2, with hot solder dip (Finish letter A) in accordance with MIL-PRF-38535.

3.11 Radiation Hardness Assurance (RHA):

3.11.1 The manufacturer shall perform a lot sample test as an internal process monitor for total dose radiation tolerance. The sample test is performed with MIL-STD-883 TM1019 Condition A as a guideline.

3.11.2 For guaranteed radiation performance to MIL-STD-883, Method 1019, total dose irradiation, the manufacturer will provide certified RAD testing and report through an independent test laboratory when required as a customer purchase order line item.

3.11.3 Total dose bias circuit is specified in Figure 7.

3.12 Wafer Lot Acceptance: Wafer lot acceptance shall be in accordance with MIL-PRF-38535, Appendix A, except for the following: Topside glassivation thickness shall be a minimum of 4KÅ.

3.13 Wafer Lot Acceptance Report: SEM is performed per MIL-STD-883, Method 2018 and copies of SEM photographs shall be supplied with the Wafer Lot Acceptance Report as part of a Space Data Pack when specified as a customer purchase order line item.

4.0 VERIFICATION (QUALITY ASSURANCE PROVISIONS)

4.1 Quality Assurance Provisions: Quality Assurance provisions shall be in accordance with MIL-PRF-38535. Analog Devices is a QML certified company and all Rad Hard candidates are assembled on qualified Class S manufacturing lines.

4.2 Sampling and Inspection: Sampling and Inspection shall be in accordance with MIL-STD-883, Method 5005 with QML allowed and TRB approved deviations in conjunction with paragraphs 3.1.1, 3.2.1, and 3.4 of the test method.

4.3 Screening: Screening requirements shall be in accordance with MIL-STD-883, Method 5004 with QML allowed and TRB approved deviations in conjunction with paragraphs 3.1, 3.1.1, and 3.4 of the test method. Electrical testing shall be as specified in Table IV herein.

4.3.1 Analysis of catastrophic (open/short) failures from burn-in will be conducted only when a lot fails the burn-in or re-burn-in PDA requirements.

4.4 Quality Conformance Inspection: Quality conformance inspection shall be in accordance with 4.2 and 4.3 herein and as follows:

4.4.1 Group A Inspection: Group A inspection shall be performed in accordance with 4.1 herein, per MIL-STD-883, Method 5005, and specified in Table IV herein.

4.4.2 Group B Inspection: When purchased, a full Group B is performed on an inspection lot. As a minimum, Subgroups 1-4 plus 6 are performed on every assembly lot, and Subgroup B2 (Resistance to Solvents / Mark Permanency) and Subgroup B3 (Solderability) are performed prior to the first shipment from any inspection lot and Attributes provided when a Full Space Data Pack is ordered. Subgroup B5 (Operating Life) is performed on each wafer lot. This subgroup may or may not be from devices built in the same package style as the current inspection lot. Attributes and variables data for this subgroup will be provided upon request at no charge.

4.4.2.1

Group B, Subgroup 2c = 10%	Group B, Subgroup 5 = *5% (*per wafer or inspection lot whichever is the larger quantity)
Group B, Subgroup 3 = 10%	
Group B, Subgroup 4 = 5%	Group B, subgroup 6 = 15%

4.4.2.2 All footnotes pertaining to Table IIa in MIL-STD-883, Method 5005 apply. The quantity (accept number) of all other subgroups are per MIL-STD-883, Method 5005, Table IIa.

4.4.3 Group D Inspection: When purchased, a full Group D is performed on an inspection lot. As a minimum, periodic full Group D sampling is performed on each package family for each assembly location every 26 weeks. A generic Group D Summary is provided when a full Space Data Pack is ordered.

4.4.3.1 Group D, Subgroups 3, 4 and 5 = 15% each (Sample Size Series).

4.4.3.2 All footnotes pertaining to Table IV in MIL-STD-883, Method 5005 apply. The quantity (accept number) or sample number and accept number of all other subgroups are per MIL-STD-883, Method 5005, Table IV.

4.5 Deliverable Data: Deliverable data that will ship with devices when a Space Data Pack is ordered:

4.5.1 Lot Serial Number Sheets identifying all devices accepted through final inspection by serial number.

4.5.2 100% attributes (completed lot specific traveler; includes Group A Summary)

4.5.3 Burn-In Variables Data and Deltas (if applicable)

4.5.4 Group B2, B3, and B5 Attributes (Variables data, if performed on lot shipping)

4.5.5 Generic Group D data (4.4.3 herein)

4.5.6 SEM photographs (3.13 herein)

4.5.7 Wafer Lot Acceptance Report (3.13 herein)

4.5.8 X-Ray Negatives and Radiographic Report

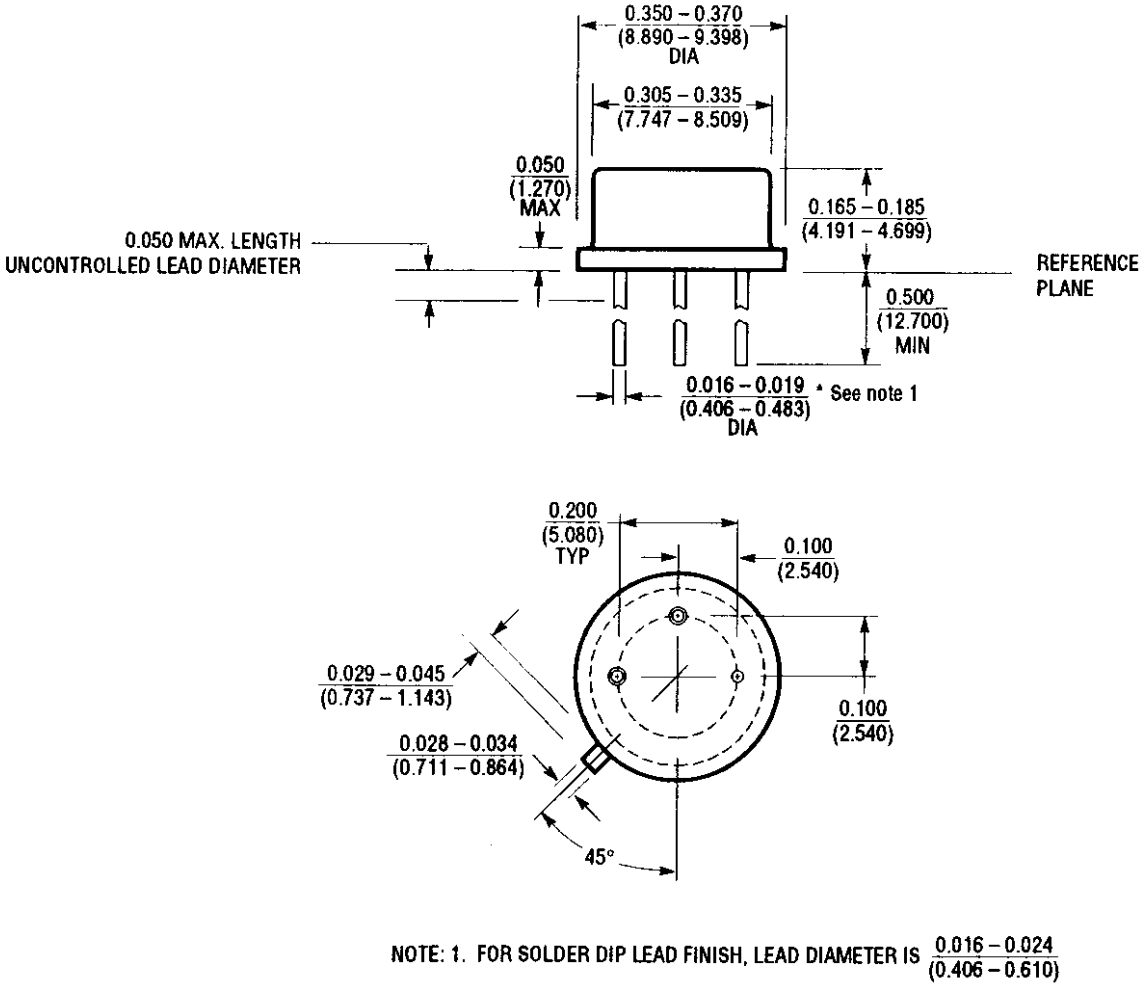
4.5.9 A copy of outside test laboratory radiation report if ordered

4.5.10 Certificate of Conformance certifying that the devices meet all the requirements of this specification and have successfully completed the mandatory tests and inspections herein.

Note: Items 4.5.1 and 4.5.10 will be delivered as a minimum, with each shipment. This is noted on the Purchase Order Review Form as “No Charge Data”.

5.0 Packaging Requirements: Packaging shall be in accordance with Appendix A of MIL-PRF-38535. All devices shall be packaged in conductive material or packaged in anti-static material with an external conductive field shielding barrier.

DEVICE OPTION #1
(H) TO39 METAL CAN / 3 LEADS CASE OUTLINE

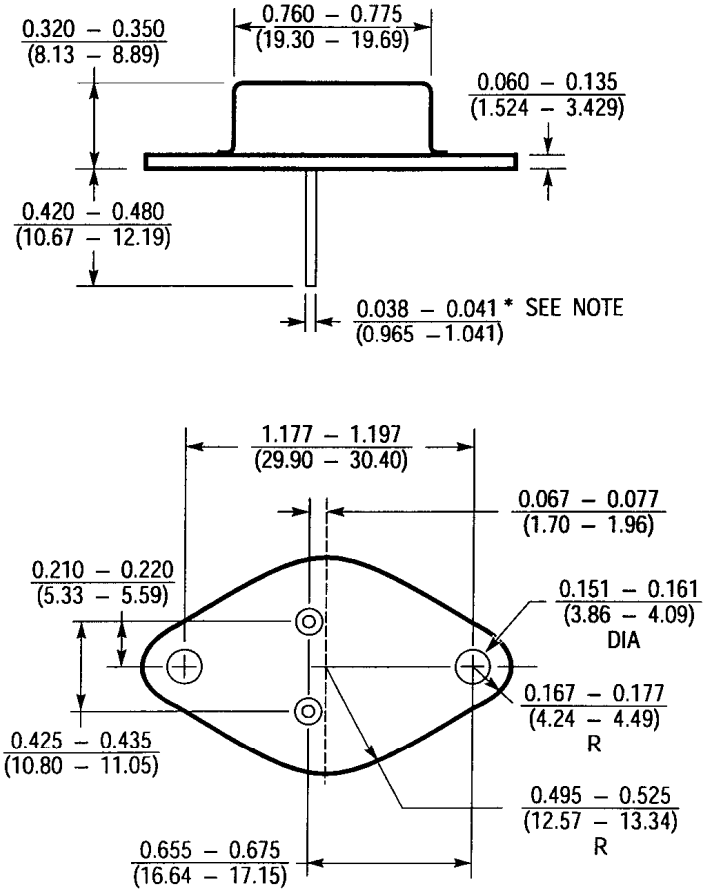


NOTE: 1. FOR SOLDER DIP LEAD FINISH, LEAD DIAMETER IS 0.016 – 0.024 (0.406 – 0.610)

θja = +150°C / W
θjc = +15°C / W

FIGURE 1

DEVICE OPTION #2
(K) TO3 / 2 LEADS CASE OUTLINE



NOTE: FOR SOLDER DIP LEAD FINISH, LEAD DIAMETER IS $\frac{0.038 - 0.044}{(0.965 - 1.118)}$

$\theta ja = 35°C/W$
$\theta jc = 3°C/W$

FIGURE 2

TERMINAL CONNECTIONS
DEVICE OPTION #1, TO39 / 3 LEAD METAL CAN

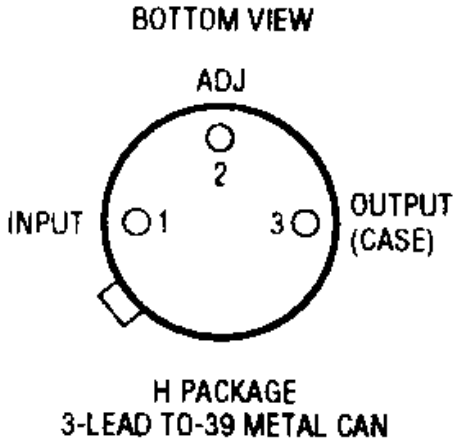


FIGURE 3

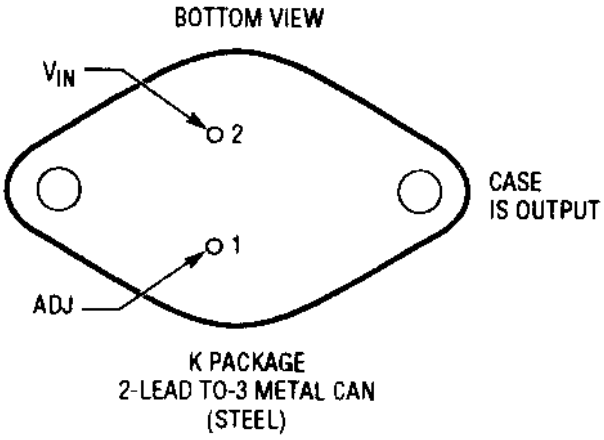
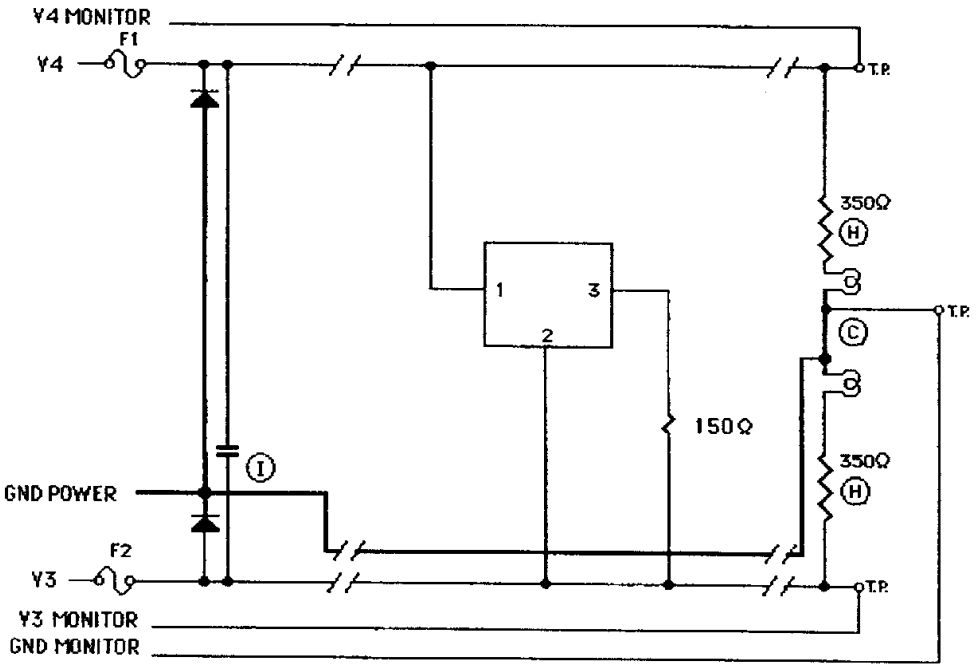
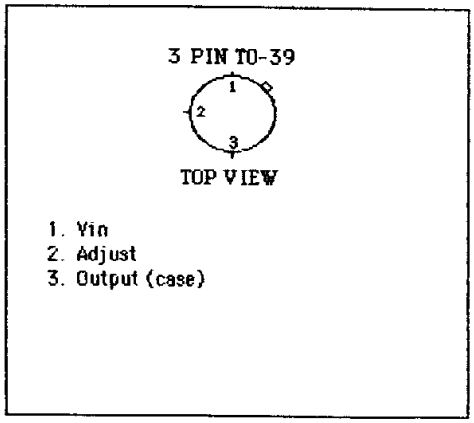


FIGURE 4

STATIC BURN-IN CIRCUIT
OPTION 1, TO39 METAL CAN / 3 LEADS



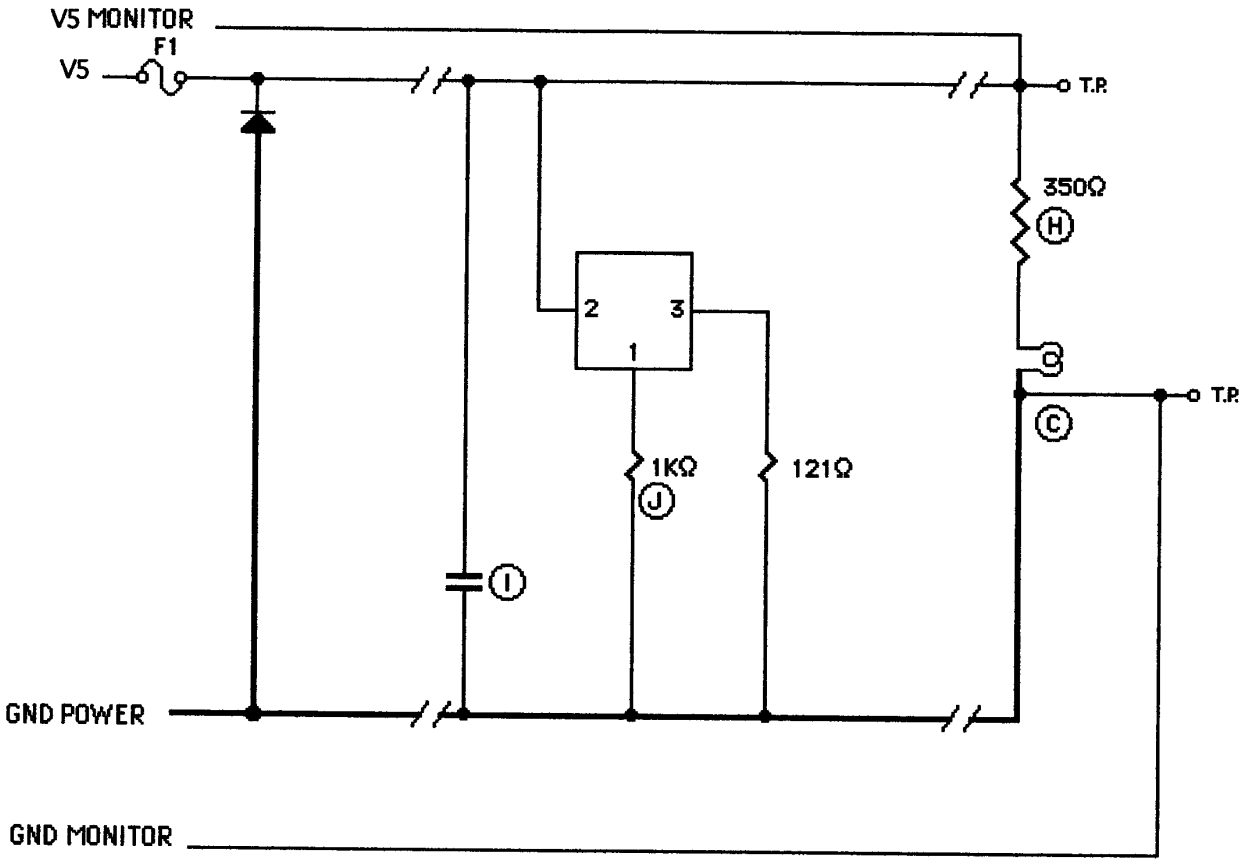
NOTES:
1. Unless otherwise specified, component tolerances shall be per military specification.
2. Tj = 174°C maximum.
3. Ta = 125°C.
4. Burn-in Voltages: V4 = +15V to +16.5V
   V3 = -15V to -16.5V



PACKAGE AND PINOUT

FIGURE 5

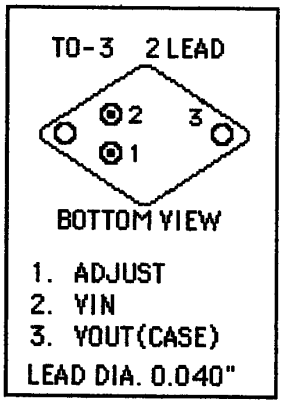
STATIC BURN-IN CIRCUIT
OPTION 2 TO3 METAL CAN / 2 LEADS



NOTES:

Unless otherwise specified, component tolerances shall be per military specification.

For RH1086:
Burn-In Voltage to be V5 = +23V to +25V
Tj = 168 °C max at Ta of 150 °C.
Tj = 143 °C max at Ta of 125 °C.



PACKAGE AND PINOUT

FIGURE 6

TOTAL DOSE BIAS CIRCUIT

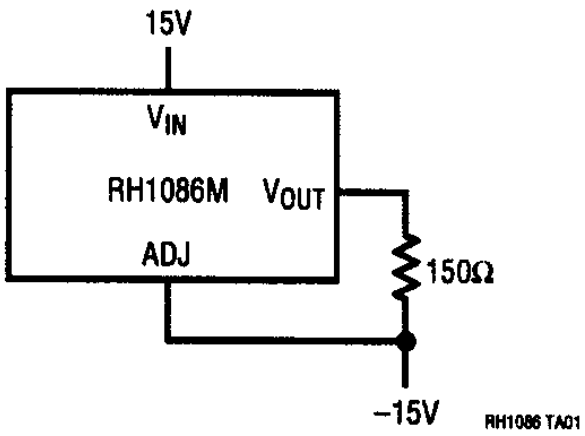


FIGURE 7

TABLE I: ELECTRICAL CHARACTERISTICS (PRE-IRRADIATION) NOTE 3

PARAMETER	CONDITIONS	NOTES	$T_A = 25°C$ MIN	TYP	MAX	SUB-GROUP	$-55°C \le T_A \le 125°C$ MIN	TYP	MAX	SUB-GROUP	UNITS
Reference Voltage	I_{OUT} = 10mA, $(V_{IN} - V_{OUT})$ = 3V (K)		1.238		1.262	1					V
	10mA ≤ I_{OUT} ≤ $I_{FULL\ LOAD}$, 1.5V ≤ $(V_{IN} - V_{OUT})$ ≤ 25V	6	1.225		1.270		1.225		1.270	2,3	V
Line Regulation	I_{LOAD} = 10mA, 1.5V ≤ $(V_{IN} - V_{OUT})$ ≤ 15V	2, 3			0.2	1			0.2	2,3	%
Load Regulation	$(V_{IN} - V_{OUT})$ = 3V, 10mA ≤ I_{OUT} ≤ $I_{FULL\ LOAD}$	2, 3, 6			0.3	1			0.4	2,3	%
Dropout Voltage	ΔV_{REF} = 1%, I_{OUT} = 1.5A (K) ΔV_{REF} = 1%, I_{OUT} = 0.5A (H)	4 4			1.5 1.25	1 1			1.5 1.25	2,3 2,3	V V
Current Limit	$(V_{IN} - V_{OUT})$ = 5V (K) $(V_{IN} - V_{OUT})$ = 5V (H) $(V_{IN} - V_{OUT})$ = 25V (K) $(V_{IN} - V_{OUT})$ = 25V (H)		1.5 0.5 0.05 0.020			1 1 1 1	1.5 0.5 0.05 0.020			2,3 2,3 2,3 2,3	A A A A
Minimum Load Current	$(V_{IN} - V_{OUT})$ = 25V				10	1			10	2,3	mA
Thermal Regulation	T_A = 25°C, 30ms Pulse				0.04	4					%/W
Ripple Rejection	f = 120Hz, C_{ADJ} = 25µF, C_{OUT} = 25µF Tantalum, I_{OUT} = $I_{FULL\ LOAD}$, $(V_{IN} - V_{OUT})$ = 3V	6	60			4	60			5,6	dB
Adjust Pin Current	T_J = 25°C			55	120	1			120	2,3	µA
Adjust Pin Current Change	10mA ≤ I_{OUT} ≤ $I_{FULL\ LOAD}$, 1.5V ≤ $(V_{IN} - V_{OUT})$ ≤ 15V	6			5	1			5	2,3	µA
Temperature Stability				0.5				0.5			%
Long Term Stability	T_A = 125°C, 1000 Hours	5		0.3							%
RMS Output Noise (% of V_{OUT})	10Hz ≤ f ≤ 10kHz			0.003							%
Thermal Resistance Junction-to-Case	Control Circuitry (K) Control Circuitry (H) Power Transistor (K) Power Transistor (H)	5 5 5 5		1.7 15.0 4.0 20.0							°C/W °C/W °C/W °C/W

SEE ALL NOTES ON NEXT PAGE

TABLE II: ELECTRICAL CHARACTERISTICS (POST-IRRADIATION)

T_A = 25°C unless otherwise noted.

PARAMETER	CONDITIONS	10KRAD (Si) MIN	10KRAD (Si) MAX	20KRAD (Si) MIN	20KRAD (Si) MAX	50KRAD (Si) MIN	50KRAD (Si) MAX	100KRAD (Si) MIN	100KRAD (Si) MAX	200KRAD (Si) MIN	200KRAD (Si) MAX	UNITS
Reference Voltage (Note 6)	I_{OUT} = 10mA ($V_{IN} - V_{OUT}$) = 3V (K)	1.234	1.262	1.230	1.262	1.225	1.262	1.220	1.262	1.205	1.262	V
	10mA ≤ I_{OUT} ≤ $I_{FULL\ LOAD}$ 1.5V ≤ ($V_{IN} - V_{OUT}$) ≤ 15V	1.220	1.275	1.219	1.275	1.215	1.275	1.210	1.275	1.20	1.275	V
Line Regulation (Notes 2, 3)	I_{OUT} = 10mA 1.5V ≤ ($V_{IN} - V_{OUT}$) ≤ 15V		0.2		0.21		0.23		0.25		0.3	%
Load Regulation (Notes 2, 3, 6)	($V_{IN} - V_{OUT}$) = 3V 10mA ≤ I_{OUT} ≤ $I_{FULL\ LOAD}$		0.3		0.3		0.3		0.3		0.3	%
Dropout Voltage (Note 4)	ΔV_{REF} = 1%, I_{OUT} = 1.5A (K) ΔV_{REF} = 1%, I_{OUT} = 0.5A (H)		1.5 1.25		1.51 1.26		1.52 1.27		1.55 1.29		1.575 1.32	V V
Current Limit	($V_{IN} - V_{OUT}$) = 5V (K) ($V_{IN} - V_{OUT}$) = 25V (K) ($V_{IN} - V_{OUT}$) = 5V (H) ($V_{IN} - V_{OUT}$) = 25V (H)	1.5 0.05 0.5 0.020		1.5 0.049 0.5 0.019		1.5 0.048 0.5 0.019		1.5 0.047 0.5 0.018		1.5 0.045 0.5 0.017		A A A A
Minimum Load Current	($V_{IN} - V_{OUT}$) = 25V		10		10		10		10		10	mA
Adjust Pin Current			120		120		120		120		120	µA
Adjust Pin Current Change (Note 6)	10mA ≤ I_{OUT} ≤ $I_{FULL\ LOAD}$ 1.5V ≤ ($V_{IN} - V_{OUT}$) ≤ 15V		5		5		5		5		5	µA

Note 1: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. Exposure to any Absolute Maximum Rating condition for extended periods may affect device reliability and lifetime.

Note 2: See thermal regulation specifications for changes in output voltage due to heating effects. Line and load regulation are measured at a constant junction temperature by low duty cycle pulse testing.

Note 3: Line and load regulation are guaranteed up to the maximum power dissipation of 15W for RH1086MK and 3W for the RH1086MH. Power dissipation is determined by the input/output differential voltage and the output current. Guaranteed maximum power dissipation will not be available over the full input/output voltage range.

Note 4: Dropout voltage is specified over the full output current range of the device. Test points and limits are shown on the Dropout Voltage curve in the LT®1086 data sheet.

Note 5: Guaranteed by design, characterization, or correlation to other tested parameters.

Note 6: $I_{FULL\ LOAD}$ is defined in the Current Limit curves in the standard data sheet. For compliance with 883 revision C current density specifications, the RH1086MK is derated to 1A.

TABLE III: POST BURN-IN ENDPOINTS AND DELTA LIMIT REQUIREMENTS

	ENDPOINT LIMIT		DELTA		
PARAMETER	MIN	MAX	MIN	MAX	UNITS
V_{OUT}	1.238	1.262	-0.01	0.01	V
$+I_{ADJ}$	15	120	-10	10	µA
V_{RLINE}	-0.2	0.2	-0.1	0.1	%

TABLE IV: ELECTRICAL TEST REQUIREMENTS

MIL-STD-883 TEST REQUIREMENTS	SUBGROUP
FINAL ELECTRICAL TEST REQUIREMENTS (METHOD 5004)	1*, 2, 3,4,5,6
GROUP A TEST REQUIREMENTS (METHOD 5005)	1, 2, 3,4,5,6
GROUP B AND D FOR CLASS S ENDPOINT ELECTRICAL PARAMETERS (METHOD 5005)	1, 2, 3

*PDA APPLIES TO SUBGROUP 1.

PDA TEST NOTE: The PDA is specified as 5% based on failures from Group A, Subgroup 1, tests after cooldown as the final electrical test in accordance with method 5004 of MIL-STD-883. The verified failures of Group A, Subgroup 1 and delta rejects after burn-in divided by the total number of devices submitted for burn-in in that lot shall be used to determine the percent for the lot.